Vishay Semiconductors





SlimSMA (DO-221AC)

| PRODUCT SUMMARY | | | | | |
|----------------------------------|--------------------|--|--|--|--|
| Package | DO-221AC (SlimSMA) | | | | |
| I _{F(AV)} | 2 A | | | | |
| V _R | 100 V | | | | |
| V _F at I _F | 0.93 V | | | | |
| t _{rr} | 25 ns | | | | |
| T _J max. | 175 °C | | | | |
| Diode variation | Single die | | | | |

FEATURES

- Hyperfast recovery time, reduced Qrr, and soft recovery
- 175 °C maximum operating junction temperature
- Specific for output and snubber operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in snubber, boost, lighting, piezo-injection, as high frequency rectifiers and freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

| ABSOLUTE MAXIMUM RATINGS | | | | | | |
|---|-----------------------------------|---|-------------|-------|--|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS | | |
| Peak repetitive reverse voltage | V _{RRM} | | 100 | V | | |
| Average rectified forward current | I _{F(AV)} | $T_{\rm C} = 155 \ ^{\circ}{\rm C}^{(1)}$ | 2 | А | | |
| Non-repetitive peak surge current | I _{FSM} | T _J = 25 °C | 65 | A | | |
| Operating junction and storage temperatures | T _J , T _{Stg} | | -65 to +175 | °C | | |

Note

⁽¹⁾ Device on PCB with 8 mm x 16 mm soldering lands

| ELECTRICAL SPECIFICATIONS (T _J = 25 $^{\circ}$ C unless otherwise specified) | | | | | | |
|--|-------------------------------------|---|------|------|------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS |
| Breakdown voltage, blocking voltage | V _{BR} , V _R | I _R = 100 μA | 100 | - | - | |
| Forward voltage | VF | I _F = 2 A | - | 0.85 | 0.93 | V |
| i orward voltage | ۷F | I _F = 2 A, T _J = 125 °C | - | 0.72 | 0.77 | |
| Reverse leakage current | | $V_{R} = V_{R}$ rated | - | - | 2 | |
| Reverse leakage current IR | I _R | $T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$ | - | 0.5 | 8 | μA |
| Junction capacitance | CT | V _R = 100 V | - | 10 | - | pF |

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RoHS

COMPLIANT HALOGEN FREE





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| DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified) | | | | | | | | |
|---|-----------------------------------|--|--|------|------|-------|----|--|
| PARAMETER | SYMBOL | TEST CO | MIN. | TYP. | MAX. | UNITS | | |
| | | $I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 50 \text{ A}/\mu\text{s}, V_R = 30 \text{ V}$ | | - | 25 | - | 20 | |
| Reverse recovery time | + | I _F = 0.5 A, I _R = 1 A, I _{rr} = 0.25 A | | - | - | 25 | | |
| Reverse recovery time | t _{rr} | T _J = 25 °C | | - | 17 | - | ns | |
| | | T _J = 125 °C | | - | 24 | - | | |
| Pools recovery ourrent | 1 | T _J = 25 °C | I _F = 2 A dI _F /dt = 200 A/μs V _R = 160 V | - | 2 | - | А | |
| Peak recovery current | recovery current I _{RRM} | T _J = 125 °C | | - | 3 | - | ~ | |
| Reverse recovery charge Q _{rr} | 0 | T _J = 25 °C | | - | 17 | - | nC | |
| | T _J = 125 °C | | - | 37 | - | | | |

| THERMAL - MECHANICAL SPECIFICATIONS | | | | | | | |
|---|-----------------------------------|--|--------------------------------|--------|------|-------|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | TEST CONDITIONS MIN. TYP. MAX. | | MAX. | UNITS | |
| Maximum junction and storage temperature range | T _J , T _{Stg} | | -65 | - | 175 | °C | |
| Thermal resistance, junction to case | R _{thJC} | Device mounted on PCB with 8 mm x 16 mm soldering lands | - | - | 12 | °C/W | |
| Thermal resistance, junction to ambient | R _{thJA} | Device mounted on PCB with 2 mm x 3.5 mm soldering lands | - | - | 115 | 0/11 | |
| Approximate weight | | | | 0.03 | | g | |
| Approximate weight | | | | 0.0011 | | oz. | |
| Marking device | | Case style SlimSMA (DO-221AC) | | 21 | -11 | | |

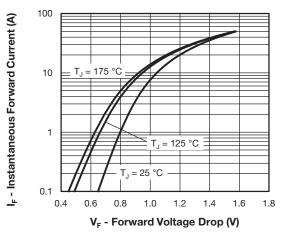
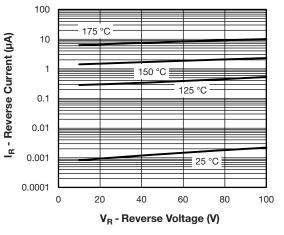
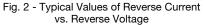


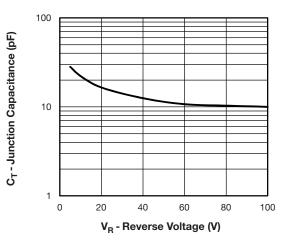
Fig. 1 - Typical Forward Voltage Drop Characteristics







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Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

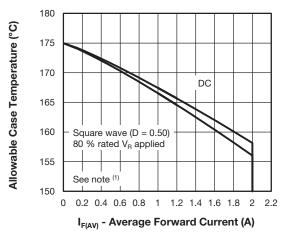


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

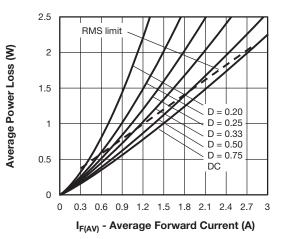


Fig. 5 - Forward Power Loss Characteristics

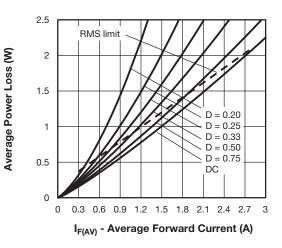
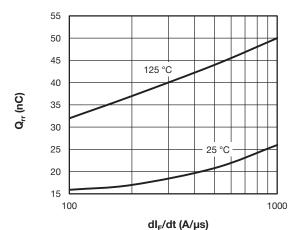


Fig. 6 - Typical Reverse Recovery Time vs. dI_F/dt



. . . .

Fig. 7 - Typical Stored Charge vs. dI_F/dt

Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

Pd = forward power loss = $I_{F(AV)} \times V_{FM}$ at ($I_{F(AV)}/D$) (see Fig. 6); Pd_{REV} = inverse power loss = $V_{R1} \times I_R$ (1 - D); I_R at V_{R1} = rated V_R

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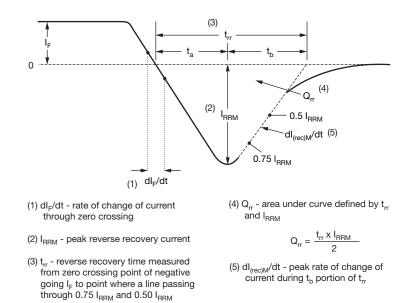


Fig. 8 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

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| Device code | VS- | 2 | Е | J | н | 01 | Н | M3 |
|-------------|-----|--------|-----------|-----------|-----------|---------|---------|---------|
| | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 |
| | 1 · | - Visl | nay Sen | niconduo | ctors pro | oduct | | |
| | 2 - | - Cur | rent rati | ng (2 = 2 | 2 A) | | | |
| | 3 - | - Circ | cuit conf | iguratior | า: | | | |
| | | E = | single o | liode | | | | |
| | 4 - | . J= | SlimSM | A packa | ige | | | |
| | 5 - | - Pro | cess typ | be, | | | | |
| | | H = | hyperfa | st recov | very | | | |
| | 6 - | - Vol | age coo | de (01 = | 100 V) | | | |
| | 7 - | . Н= | AEC-Q | 101 qua | lified | | | |
| | 8 - | - M3 | = halog | en-free, | RoHS- | complia | nt, and | termina |

extrapolated to zero current.

| ORDERING INFORMATION (Example) | | | | | | | |
|--------------------------------|-------------------|------------------------|-----------------------------------|--|--|--|--|
| PREFERRED P/N | QUANTITY PER REEL | MINIMUM ORDER QUANTITY | PACKAGING DESCRIPTION | | | | |
| VS-2EJH01HM3/6A | 3500 | 3500 | 7"diameter plastic tape and reel | | | | |
| VS-2EJH01HM3/6B | 14 000 | 14 000 | 13"diameter plastic tape and reel | | | | |

| LINKS TO RELATED DOCUMENTS | | | | | |
|-------------------------------------|--------------------------|--|--|--|--|
| Dimensions www.vishay.com/doc?95771 | | | | | |
| Part marking information | www.vishay.com/doc?95562 | | | | |
| Packaging information | www.vishay.com/doc?88869 | | | | |

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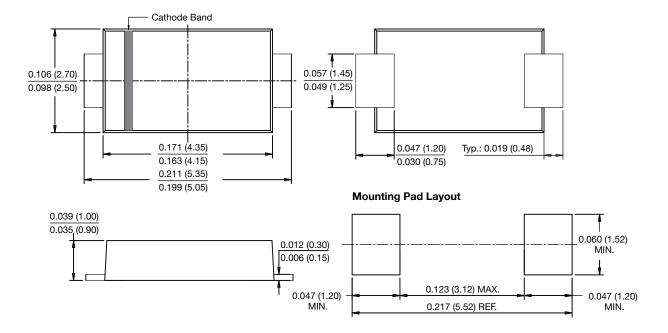
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DO-221AC (SlimSMA)

DIMENSIONS in inches (millimeters)





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